

MAGNETIC MEMORY CELL WITH PLURAL READ TRANSISTORS

ABSTRACT

A magnetic random access memory (MRAM) device has increased $\Delta R/R$ for sensing a state of a pin-dependent tunneling (SDT) device. The MRAM device includes plural transistors connected to a read line for sensing the state of the SDT device. Plural transistors lower an underlying resistance during reading, increasing $\Delta R/R$. The plural transistors can share a source region.